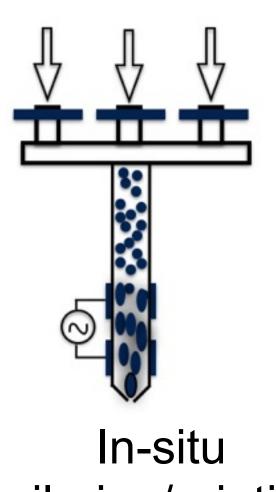
Atmospheric Pressure Plasma Jet as a Dry Alternative to Inkjet Printing in Flexible Electronics

Ram Prasad Gandhiraman¹, Arlene Lopez^{1,2}, Jessica Koehne², M. Meyyappan² ¹Universities Space Research Association, Mountain View, CA-94043 ²NASA Ames Research Center, Moffett Field, CA-94035

Abstract

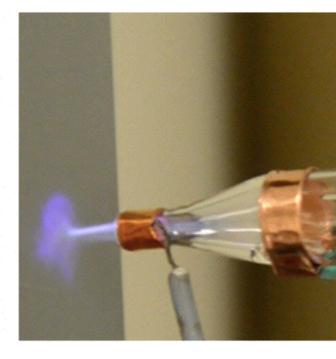
We have developed an atmospheric pressure plasma jet printing system that works at room temperature to 50 deg C unlike conventional aerosol assisted techniques which require a high temperature sintering step to obtain desired thin films. Multiple jets can be configured to increase throughput or to deposit multiple materials, and the jet(s) can be moved across large areas using a x-y stage. The plasma jet has been used to deposit carbon nanotubes, graphene, silver nanowires, copper nanoparticles and other materials on substrates such as paper, cotton, plastic and thin metal foils.

Plasma Jet Multi-Material Printer



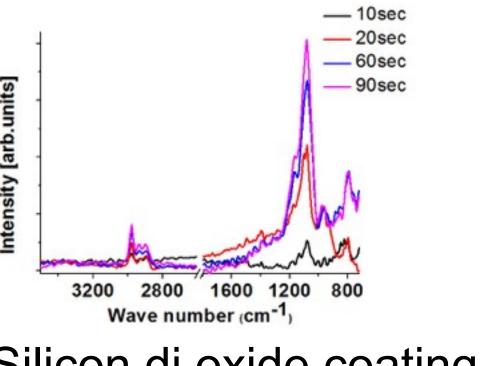


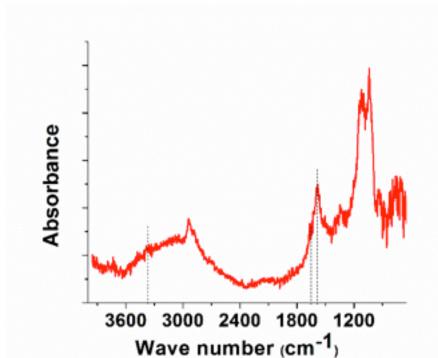
Plasma Off



Plasma On

Low & High K Dielectric Coating





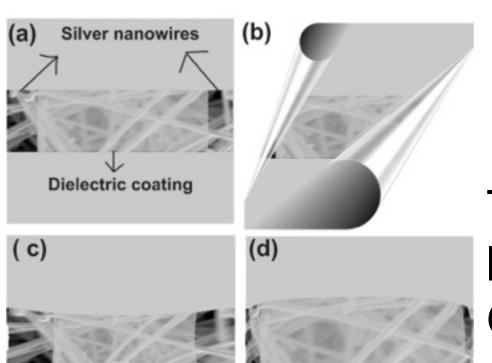
tailoring/printing

In-line additive manufacturing

•Nanocolloids, organic materials etc. transported as aerosol by carrier gas

- Precise control over thickness and morphology
- •Ability to tailor material properties in situ (chemical, electronic)
- •Can be combined as an in-line manufacturing process in additive manufacturing

Silicon di oxide coating



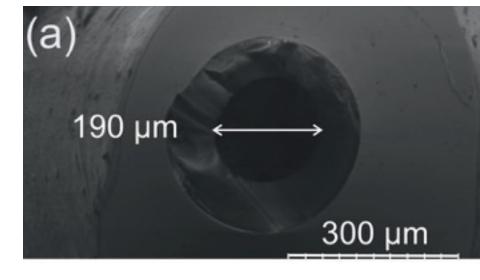
Nitrogen-incorporated silicon oxide coating

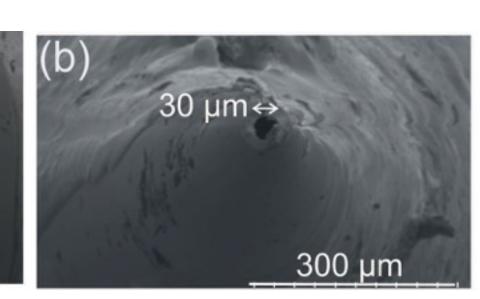
Thin gate dielectric, passivation layer in microelectronics Optical waveguides (varying refractive index)

Plasma Jet Printed Electronics









Scanning electron microscopic image of Nozzle

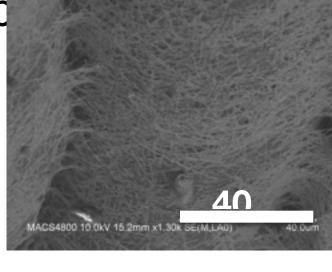


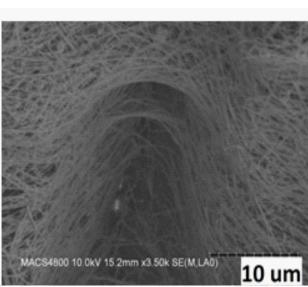
Plasma printed

on PET bottle



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Copper on poly imide

antenna structure

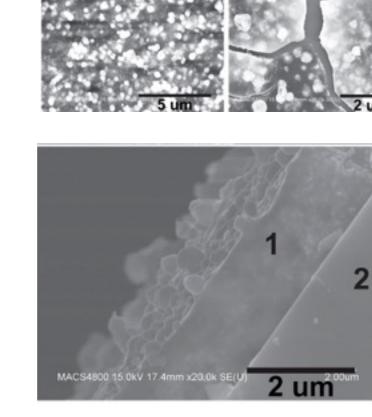
On PET bottle On paper

Silver nanowires on 3D printed ABS plastic

In-situ Tailoring of Material Properties

In-situ reduction of Cu2+ to metallic copper 60000 50000 40000 € 30000 gg 20000 10000 960 Cu L edge XAS^{mono} No post processing, No pre-post 20 um 10 um thermal treatment Printed using same colloid

Controlled surface characteristics Contacts & Reference



Cross sectional

SEM of Cu(1) on Silicon(2)

Email: m.meyyappan@nasa.gov

Email: ramprasad.gandhiraman@nasa.gov

(1)Three US Patent applications pending

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- (3) Ram P. Gandhiraman et al., ACS Appl Mater Interfaces. **2014**, 6, 20860
- (4)Ram P. Gandhiraman, Dennis Nordlund, Vivek Jayan, M. Meyyappan, Jessica E. Koehne. ACS Appl Mater Interfaces. 2014, 6, 22751.
- (5)<u>https://www.sciencedaily.com/releases/</u> 2016/03/160322120038.htm